This log sheet is now on the computer

OXFORD 80+ RIE ETCH/PECVD SYSTEM LOG SHEET-*Please fill out as completely as possible for characterization and maint*

Name/Date	Recipe Used	Base Pressure (mT)	Deposition or Etch Gas(es)	Gas #s	Gas Flow Rate(s) (sccm)	Gas Flow Setting (%)	Throttle Pressure (mT)	Power Setting (% Pmax)	Forward Power (Watts)	Material Etched or Deposited	Dep/ Etch Time	Temp (C)	Measured Etch/dep Rate (um/min)	Results/Problems/Maintenance/Etc.
Lara Barnes 8/11/10	aunanocs. rec	20	Ar		9.1				100	Au	23 min.			
Luciano Aguirre 8/13/10	Sopo2		O_2		50				200	PR	3			Chamber B
Lara Barnes 8/17/10	aunanocs. rec	20	Ar		9.1				100	Au	23 min			
CTaylor 8/17/10	agnano cs	20	Ar		15				80	Ag	18 min			
David W 9/1/10	smartch		Ar		50				200	ITO	40min			
Sandeep 9/1/10	Chclean	1	—		—				200			300		Chamber clean pump
Sandeep C 9/1	bbSiO2 @				3 (slow)				200	SiO_2	2 min			
Karuna 09/02/10	Fkc SiN	—	—		—				100W		100 min ea			
DavidW	Ozetch		O_2							Photoresist	4 min			
DavidW	drsinx		SiH_4 N_2		7 426				24	SiNx	2:20 min ss	225		Chamber A
David W	hgsinx1		SF_6		26				100	SiNx	2:35			
Sandeep C	cfSiO2		N_2O SiH_4		250 6 sccm				20	SiO_2	10 min	302		Chamber
Bennion Redd	Sopsin	74	O_2 SF_6		7.5 26				60	Si_3N_4	7:00	22		

Please fill out Both.

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CTaylor 10/6/10	agnano cs	20	Ar		15				80	Ag	18min 20 min			
CBarnes 10/11/10	aunano cs	20	Ar		10				100	Au	23min			
CTaylor 10/14/10	agnano cs	20	Ar		15				80	Ag	6x21min 2x8min			
DavidW 10/14/10	snoretch	20	Ar		50				200	ITO	20			X 3
CBarnes 10/15/10	aunanocs	20	Ar		10				100	Au	23 min			4 runs
David W 10/21/10	hssinxl	40	SF6		26				100	aSi	2:35 mss			didnt remove [illegible] [illegible] has always [illegible] before
DavidW 10/21/10	snoretch	20	Ar		50				200	ITO	30			
CBarnes 11/1/10	aunano cs	20	Ar		10				100	Au	23			2 runs
CBarnes 11/2/10	aunano cs	20	Ar		10				100	Au/poly styrene	23			2 runs
David W 11/18	snoretch	20	Ar		50				200	ITO	25			

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CHARLES F	–													CHAMBER A - LOOKING BETTER
ANDREW M.	5b02 rec		O_2							DEP-PPV polymer	10 min		1.8μm/min	
CHARLES F	–													CLEANING CHAMBER A
[illegible]	[illegible]									[illegible]	1 min 5 [illegible]			
[illegible]	[illegible]		Ar		50				200W		10 [illegible]			
CHARLES 7/27														CHAMBER A
[illegible] 7/27	[illegible]		SiH_4 N_2		7 ~26				24W	SiNX	2:35			chamber A
[illegible] 7/29	"		"		"				"	"	"			"
C Taylor 8/3/10	agnano cs	20	Ar		10			~~100~~	100	Ag	20 min			
C Taylor 8/4/10	agnano cs	20	Ar		15				150	Ag	8-12 min			
Carabarnes 8/5/10	aunanocs	20	Ar		9.1				97.2	Au	23 min.			
Luciano Agnano 8/6/10	[illegible]	~~50~~	O_2		50				200	PR	4 min			chamber B
C Taylor 8/11/10	agnano cs	20	Ar		15				100	Ag	15min			

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Charles Fisher		1200							30	SiO_2	10m	300		shower head
9/16 Steve	tungsten	40	SF6 O2 CF4		9.7 2.6 25.8				97.5	TiW	10min	24		
"	"	"	"		"				"	"	15min	"		
"	"	"	"		"				"	"	2min	"		
"	tiwetch	"	O2 CF4		2 42				306.9	TiW	10	"	~10nm/min	
~~"~~	~~"~~	~~"~~	~~"~~		~~"~~				~~"~~	~~"~~	~~3~~	~~"~~		aborted
9/16 Steve	tungsten	40	SF6 O2 CF4		9.7 2.2 25.8				97.5	TiW	5	24	8-10 nm/min	
"	"	"	"		"				"	"	"	"	"	"
"	"	"	"		"				"	"	15	"	"	"
"	"	"	"		"				"	"	30	"	"	"
Steve 9/17	"	"	"		"				"	"	35	"	"	"
Cara Barnes 9/20	aunano cs.rec	20	Ar		9.1				96.9	Au	23 min	13		
[illegible]	[illegible]	40	O2		50				200	[illegible]			"	

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Cara 7/8 Barnes	avnanocs. rec	26	Ar		9.1				98.4	Au	23 min	14		
~~Steve~~ 7/9 M&D	tungsten rec		SF6 O2 CF4		9.7 2.6 25.9				97.5	W	9	24	25?	
CTaylor 7/12	avnano cs.rec	25	Ar		9.1				97.8	Ag	30 min	14		chamber not pumped down over night, took 60 minutes
~~Steve~~ D 7/12	tungsten	40	SF6 O2 CF4		9.7 2.6 25.7				97.5	W	15 min	24		
CHARLIE F 7/1	—	—	—	—	—				—	—	—	—	—	REPLACE O RINGS/LEAK CHECK CHAMBER A CAN CLEANING RECIPE
CHARLIES FRIEND 7/12														ON CHAMBER A - WORKED
CHARLIES FRIEND 7/12	dtsio2	1.250	N20 SiH4	250 → 6 →					20	SO_2		300	?	STILL HAVE SHOWERHEAD MARKS
Steve M&D 7/12	bbcr etch rec		Cl2		20				307	Cr	20	3		
CTaylor 7/13	avnano cs.rec	25	Ar		9.1				97.8	Ag	40 min	14		
Steve 7/13 M&D	tungsten	40	SF6 O2 CF4		9.7 2.6 25.8				97.5	W	30 min	24		
" 7/13	"	"	"		"				"	"	5 min	"		
" 7/13	"	"	"		"				"	"	5 min	"		
CTaylor 7/14	agnano cs.rec	15	Ar		20				203.4	Ag	25min	6		

PLASMALAB RIE ETCH SYSTEM LOG SHEET-*Please fill out as completely as possible for characterization and maintenance.*

Name/Phone	Date	Base Pressure (mT)	Etch Gas(es)	Gas #s	Gas Flow Rate(s)	Throttle Pressure (mT)	Power Setting (% Pmax)	Forward Power (Watts)	Reverse Power (Watts)	Match Network Tune Value	Match Network Load Value	Material Etched	Etch Time	Measured Etch Rate (um/min)	Results/Problems/Etc.
Steve 801-755-4895	6/22		CF4 O2 SF6		10 3.5 26.0			97.5	11-14			W	8+8+26		~~Tungsten~~. rec
Compac	6/24		O_2									Photo resist AZ4260	5 min		
Cara Barnes	6/24	20	Ar		10			97.5				Au	23 min		
Albright- 8015579844	6/25		O_2		50 sccm			200				Parylene	30 sec.		Surface etch.
Steve 801-755-4895	6/25		CF4 O2 SF6		10 3.5 26.0			97.5	11-14			W	40 min		Tungsten. rec
Steve	6/28		"		"			"	"			W	45		" "
Steve	6/28		C—									Photo resist	4 min		1815 clean
Albright 8015579844	6/29		O_2		50 sccm			200				Parylene	30 sec.		
Steve	6/30		CF4 O2 SF6		10 3.5 26.0			97.5	11-14			S. 11 W	25		
Albright 8015579844	6/30		O_2		50			200				Parylene	7:00 min		
Cara Barnes	7/7	24	Ar		9.1			97.8				Au	23 min.		took ~10 times longer than usual to pump to base pressure
Steve	7/6		CF4 O2 SF6		10 3.5 26			97.5	11-14				12 min		
Steve	7/7		"		"			"	"				60 min		

OXFORD 80+ RIE ETCH/PECVD SYSTEM LOG SHEET-*Please fill out as completely as possible for characterization and maint*

	Name/Date	Recipe Used	Base Pressure (mT)	Deposition or Etch Gas(es)	Gas #s	Gas Flow Rate(s) (sccm)	Gas Flow Setting (%)	Throttle Pressure (mT)	Power Setting (% Pmax)	Forward Power (Watts)	Material Etched or Deposited	Dep/ Etch Time	Temp (C)	Measured Etch/dep Rate (um/min)	Results/Problems/Maintenance/Etc.
B	J. Goeckeritz 6/15/09	jersf02	6.5x10-5	SF6 O2	20.1 2.0				223		Si	5		2um/5min	
B	Sandeep C 6/17/09	thpoly.th	"						25		Poly	~~[illegible]~~ 30 sec.			
6bsio2 A	Sandeep C 6/17/09	PECVD oxide	"						200		oxide	40 min			
B	C Taylor 6/19/09	aunano cs	$1 \cdot 10^{-4}$	Ar		9.1			100		Au	22min	23.0		
B	C Taylor 6/24/09	aunanocs	$1 \cdot 10^{-4}$	Ar		9.1			100		Au	22min	23.0		
B	J. Goeckeritz 6/26/09	jersf02	6.5x10-5	SF6 O2	20.1 2.0				223		Si	60min			
HSSINX4 B	McCauley 7/2/09	HS SiNx	6.5x10-5	SF6	~~[illegible]~~ 20				~~[illegible]~~	100	A-Si:H	3min			HSSINX1.
wercr B	07/08/09 Jeremy	B-chamber	~~O2~~												Oxygen plasma on ETO recipe. tried to figure out
B	07/10/09 Jonghun	j-Cl2	6E-5	Cl2							Al.				test y
B	07/11/09 Jonghun	j-Cl2	6E-5	Cl2							Al				test y
B	07/13/09 Jonghun	j-Cl2	6E-5	Cl2							Al				test y
B	07/14/09	j-Cl2	6E-5	Cl2							Al				test
A	7/15/09 J. Goeckeritz	[illegible] Si3N4	6.5x10-5	SiH4 N2O	[illegible]	[illegible]			200		Si3N4		300		

~~jgsin6~~

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B	Kamdem 07/17/09	carbon etch	6E-5								Carbon nanotube	15"			
B	Srinivas 7/22/09	SiO2 etch									SiO2	36 Sec			
B	[illegible] 12	SiO2 etch	6.5e-5	CF4		40 sccm		75mT	[illegible]	100W		~16nm/min			
	Srinivas Mergu	O2 clean	6e-5	O2		30 sccm				200W					
A	Sandeep	bbSiO2	6e-5	PECVD oxide						20W	Oxide (dep)		300 C		
B	Raj	snps etch		O2		50 sccm				50 W	Photo resist		2 Hr.		
A	Sandeep	Ch clean	150T							150W			300C		
A	Sandeep	bbSiO2 (PECVD)	6e-5	oxide						20W	oxide		300C		
B	CTaylor	aunano CS	1.10-4	Ar		9.1				100W	Au	22min	23°C		
	Xian 2019	ICLM [illegible]	0.1	O2		50 sccm				200W	Parylene	30 min	23°C.		
	[illegible] 03/06 Dane McCamey	syl ZnO sn	(4.10-4)	CF4		25				200	ZnO	40 min	12°C		
	Song-Yun 03/10	snor etch	4.10-4	Ar		50				200	ZnO	40 min	11°C		
	Song-Yun 03/12	snoretch	4.10-4	Ar		50				200	ZnO	40 min	11°C		

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Xiaojin 9/15/09		4x10-5	Cl_2 Ar		20 20		15 15	300W 300W		Cr Au	2:30 4:00			
Kai Yang 9/16/09	SiN etch	0.15	CF_4		20					SiN		27		
C Taylor 9/16/09	au nanocs	1·10-4	Ar		9.1				100W	Au	20min	23.0		took ~4x longer than normal to pump to base pressure
Xiaojin 9/16/09		4x10-5	Cl_2 Ar		20 20		15 15	300W 300W		Cr Au	2:30 4:00			
Seong-Yun Lee 9/18/09	SiN	0.01	SiH_4 N_2		2 426			24 W		SiN	18min	100[illegible]		
Kai Yang 9/17/09	SiN	0.15	CF_4		20					SiN		27		
Kai Yang 9/23/09	SiN	0.15	CF_4		20					SiN		27		
Xiaojin 09/23/09		4x10-5	Cl_2 Ar		20 20		15 15	300W 300W		Cr Au	2:30 4:00			
Seong-Yun Lee 9/24/09	[illegible]	4x10-4	SF_6		26			100W		SiN_x	1:35	24		
Kai Yang 9/25/2009	SiN	0.15	CF_4		20					SiN		27		
Richard Morrill 9/25/09	SiO_2 SiO_2 250 PECVD	10 mT	N_2O (SiH4 crossed out) SiH_4		308 (crossed out) 3[illegible]				30.5	SiO_2	30 min	225		Temp fluctuated from 223-2[illegible]. After every 5 min of Dep time, I would stop and adjust Temp for 5 min.
Will Baker 8/28/09	dnmsin SiN dep	[illegible]	NH_3 SiH_4		26 20			low		SiN	12min	300		

Problem: Grey [illegible] on wafer, looks as if SiO_2 was [illegible] deposited in [illegible] [illegible]

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MICRO-SENSORS ROHIT 9/29	CF_4/ O_2	150	CF_4	O_2	40/4				200	Etched Si_3N_4	5min	—	—	
Jenny Goodwin 9/29	[illegible]	7×10^{-5}	Cl_2		20			[illegible]	300	Cr	5m 40s	RT	~6nm/min	
[illegible] 10/01/05	CF_4 O_2	[illegible]	[illegible]	[illegible]	[illegible]				500	Etched Si_3N_4	3 min			
Raj	snb'r etch		O_2		50 sccm				200 W	Parylene	25 min			
J. Crockett	O_2 clean	$7\times10^{-?}$	O_2		50				100	5813	10 min			
Abhijit	O_2	4×10^{-4}	O_2	O_2	50		0.1	~~200~~ V	200	Parylene	6 min.			
JamYang 11/4	Cl_2/Ar	4×10^{-6}	Cl_2		50/30	50		150W		poly	20min			
JamYang 11/5	Cl_2/Ar	4×10^{-6}	Cl_2		10/30			150W		poly	20min			
[illegible]	[illegible]	[illegible]	[illegible]		[illegible]			[illegible]	[illegible]	[illegible]	[illegible]			
[illegible]								[illegible]						
Abhijit	O_2	4×10^{-4}	O_2	O_2	50		0.1		200	Parylene	5+5 mins			
MOHIT	CF_4	2.5×10^{-5}	Etch gas CF_4		42		0.02	~~200~~	200	SOG on Si	40 nm/min.			
Qiurong	O_2	0.1	O_2	O_2					200	Parylene	30/sec	RT		

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[illegible]	[illegible]	[illegible]	N_2O SiH_4	[illegible] 3			500		30.5	[illegible]	[illegible]	300	25.nm ~~734~~ 73 l nm/min	
Charles Fisher	NONE	NA	NA	NA										CHECKED OIL IN PUMPS
Tony O	SiO_2+225	~~225C~~	DEP	N_2O SiH_4	328 3		500		30.5	SiO_2	3000	225	1.25 nm 41.2 nm/min	
[illegible]		100	O_2		50		100	100	100	PR		25		
Norrill, Rich 12-17-09	SiO_2+225	10mT ~~0.040~~	Dep	N_2O SiH_4	308 3.0		500		30.6	SiO_2 deposited	10:00	225C	887.0nm 88.7 nm/min	
MOHIT MENON 12/22	[illegible]	[illegible]	Etch CF_4	4	42		0.020	200W		Etch SiO_2	[illegible]	RT	[illegible] nm/min	
Sandeep C	6b SiO_2	~~500~~ [illegible]	Dep	N_2O SiH_4	[illegible] 3			20W	30W	SiO_2	12 min	300C		
MOHIT 12/28 MENON	SCG	2×10^{-5}	Etch CF_4		42		0.020	200W		Etch SiO_2	1m 45sec	RT	~7 nm/min	

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[illegible]	[illegible]		O_2		[illegible]				50	[illegible]	6 min			
[illegible]	[illegible]								[illegible]	[illegible]	[illegible]			
Kar Yay	SiO_2 dixa	500	N_2 SiH_4	308 3			500		30.5	SiO_2	845	300		
[illegible]	[illegible]		[illegible]						[illegible]	[illegible]	8	[illegible]		
Xiaodong	aresled	1×10^{-4}	O_2/Ar		50/10				[illegible]	clean		23		
Greg Liddiard 14 FEB	blanket		O_2 SF_6							Poly Si	1 min			
W. Baker	SiN_x Dave's		N_2 SiH_4		20 420					SiN	8 min	225		all went well temp was stable
Rafael	O_2		SF_6							poly Si				
[illegible]	~~blanket~~ bbpolyset		"							"	2 min			"
Faisal	O_2 SF_6	4×10^{-4}	O_2 SF_6		20 26.0				200	Si	15 min	15	0.4 mm/min	4" Si wafer 90% open
Charles Fisher	—	—	—	—	—	—	—	—	—	—	—	—	—	REPAIR WORK 8:00 Am – 3:30 Pm
" "	SF_6	4×10^{-4}	SF_6		20				200	Si	25 min			

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Devon Newman 3/15/10	SF_6 sicetch5	50	SF_6 O		26 1				300W	SiC	240 min			
[illegible]+Ting 3/18/10	bp eth2		O_2		50				200W	Si				
Jiewen+Jing 3/17/10	ArO_2 etch		O_2 Ar											
MOHIT(7-9462) 03/29	SOG-etch	2.5×10^{-5} T	Etch CF_4		42			~~200W~~	200W	SiO_2	Etch		17.1 nm/min	
TON4 O	TLO PLYET	6.5E-5	ETCH SF_6,O_2		O_2 13.0 SF_6 20.1				223W	POLY	1.0Mi	—		
Craig L. 04 APR 2010	lbpolyet									Si (Poly) Nitride	10min			
C Taylor 4/13/2010	aunano ncs	1.0×10^{-4} mbar	Ar		10				100W	Au	23min	18°C		
MOHIT(MENON) 7-9462	SOG-mo	3×10^{-5}	CF_4		42		0.020	200	200	Etch SiO_2		RT		
MOHIT/MENON 7-9462	SOG-mo	3.0×10^{-5}	CF_4		42		0.020	200	200	Etch SiO_2			~15nm/min	
Kamilu 05/06/10	~~[illegible]~~ thsinet	4×10^{-4}	CF_4 O_2		35 35		0.075	200		Etch SiN	1min	RT		
Raheel 5/6/2010	bpreth2	26	O_2		49.6			200	200	[illegible]	15min			
Paul Cole 5/6/10														N_2 purge PECVD
Charles Fisher														Chamber A repair complete

OXFORD 80+ RIE ETCH/PECVD SYSTEM LOG SHEET-*Please fill out as completely as possible for characterization and maint*

Name/Date	Recipe Used	Base Pressure (mT)	Deposition or Etch Gas(es)	Gas #s	Gas Flow Rate(s) (sccm)	Gas Flow Setting (%)	Throttle Pressure (mT)	Power Setting (% Pmax)	Forward Power (Watts)	Material Etched or Deposited	Dep/ Etch Time	Temp (C)	Measured Etch/dep Rate (um/min)	Results/Problems/Maintenance/Etc.
CHARLES FISHER 5/13	80 SiO2	1000	N2O SiH4		300 3				30	SiO2	20:00	300		PLASMA NOT STAYING LIT
CHARLES FISHER 5/13	CfSiO2	1000	N2 N2O SiH4		161.3 780 8.5		1000	20	20	SiO2	2000	300		PLASMA LOW BUT STAYING LIT.
MOHIT (MENON) 7-9462	SOG-MO	300	CF4		42		20		200	Etch SiO2				
Richard 5.23.2010	bprete		O2				20		200	PR SU-8				
CHARLES	SfSiO2	1000	N2O SiH4		700 3		1000		25	SiO2	12min			~GETTING THERE
CTaylor 6/4/10	aunano CS	20	Ar		10				100	Au	23min	23		
CHARLES FISHER	CfSiO2	1000	N2O SiH4		250 6		1000		20	SiO2	5min / 15min	300		
~~CHARLES FISHER~~	~~cfsio2~~	~~1000~~	~~N2O SiH4~~		~~250 6~~		~~1000~~		~~20~~	~~SiO2~~				
Abhijit	66 Paryln	4x10-4	O2		50				50	Parylene	30 sec			
CTaylor 6/11/10	aunano CS	20	Ar		10				100	Au	23min	23		
Sung-Yun 6/14/10	hirinxl.re ITOetch.re	10mT	SF6 Ar		26 40				100	a-Si ITO	4min 35min			
CBarnes 6/16/10	Au nano CS	20	Ar		10				100	Au	23 min	23		
CTaylor 6/17/10	agnano CS	50	SF6		10				100	Ag	15min	23		
Sung-Yun 6/14/10	drmsiry	300	SiH4 N2		2 475				20	SiNx	15min	225		

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Raj 06/09/10	8Omit	6x10-5	SF_6 / O_2		26 / 26			100W / N	100W	Silicon	1 Hr			
David W 9/23/10	snafetch	4e-4	Ar		50			[illegible]	300W	ITO	45min			
David W 9/23/10	O2etch	4e-4	O_2		50				200W	Photoresist	Etch N:25			
Abhijit M. 9/27/10	bbO2etch	4e-4	O_2		50				200	PR Parylene	30+30 sec.			
David W 9/27/10	snafetch	4e-4	Ar		50				200	ITO	30min			
Abhijit M 9/28/10	bbparylene	4e-4	O_2		50				200	Parylene	7+7 +7min.			
Bennion R 9/30/10	bbocetc2	4e-4	O_2		50				200	Etch LOR+PR	10 min.			
David W 9/30 [illegible]	snafetch	4e-4	Ar		50				200	ITO	30min			
Bennion R 10/7/10	Sop cf4o2													
Luciano Aguirre 10/19/10	SOPAu	4x10-4	Ar		20				200	Au	12min			Gold not etched uniformly - esp near edges/corners of 3x3 glass plate
	SOPCF4O2	4x10-4	CF_4 O_2	X	35 3.5				200	Ti	50sec			
Luciano Aguirre 10/20/10	SOPAu	4x10-4	Ar		20				200	Au	13:15			
	SOPCF4O2	4x10-4	CF_4/O_2		35/3.5				200	Ti	30sec			
Luciano Aguilar 10/20/10	SOPAu	4x10-4	Ar		20				200	Au	12:00			
	SOPCF4O2	4x10-4	CF_4/O_2		35/3.5				200	Ti	30sec			
Luciano Aguirre 10/21/10	SOPAu	4x10-4	Ar		20				200	Au	12:30			Valve stuck during vent about 4 min wait rec worked
	SOPCF4O2	4x10-4	CF_4/O_2		35/3.5				200	Ti	30sec			

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Name/Phone	Date	Base Pressure (mT)	Etch Gas(es)	Gas #s	Gas Flow Rate(s)	Throttle Pressure (mT)	Power Setting (% Pmax)	Forward Power (Watts)	Reverse Power (Watts)	Match Network Tune Value	Match Network Load Value	Material Etched	Etch Time	Measured Etch Rate (um/min)	Results/Problems/Maintenance/Etc.
Lucas Aguirre 10/20/10			Ar		30			200				Ag	1:30		SUP Ag
		4x10^-4	CF4/O2		35/3.5			200				Ti	20sec		SUP CF4 O2
Bennion Redd 801-471-5031	21 Oct 10	$4x10^{-4}$	CF_4 O_2		35 3.5			200				SiN	20 min		SOP SiN
Hyunjeong Kim	11/05/10	$4x10^{-4}$	SF_6		20 sccm	50mtorr		70W				Mo78Ge22	2min 40sec	400Å/160sec	clear etching
David W	11/10	[illegible]	Ar		[illegible]			200				ITO	30min		
Hyunjeong Kim	12/03/10	$4x10^{-4}$	SF_6		20 sccm	50mtorr		70W				Mo70Ge30	3min 23sec		clear
〃	12/31/10	$4.4x10^{-4}$	SF_6		〃	〃		〃				Mo70Ge30	25sec		
Kamden	01/04/11	$4x10^{-4}$	SF_6		23 sccm	50mT		100W				SiN	6min		
Kamden	01/04/11	$4x10^{-4}$	O_2		23 sccm	50mT		100W				resist	7 min		
Kamden	01/05/11	-11-	SF6		26sccm	50mT		100W					2 min		
Kamden	01/06/11	-11-	SF6		26sccm	50mT		100W					90sec		
Kamden	01/06/11	-11-	O_2		35sccm	50mT		100W					8 min		
Kamden	01/12/11	-11-	SF_6		26sccm	50mT		100W					2 min		
HJ Kim	01/21/11	$4x10^{-4}$	SF_6		20sccm	50mtorr		70W				MoGe	25sec		

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Ryan Bock 5013373551	1/26/11		CF_4	1	25			225	2.6			Si_3N_4	3:45		
Kamdem 8015889716	1/31/11		Cl2 i_2		40 2			150	5.1			Aguide	10:30		
Kamdem 8015889716	2/02/11		SF6 O_2		26 26			100 50				SiN PR	2' 10'		
Kamdem 8015889716	2/03/11		SF6 O2		26 26			150 50				SiN PR	2' 10'		
Kamdem 8015889716	2/04/11		SF_6 O_2		26 26			100 50				SiN PR	2' 10'		
R. Bock 801 839 3551	2/10/11		CF_4	1	25			225	2.6 3.8			Si_3N_4	6 3:45		
CTaylor 8015813816	2/17/11		Ar		10			100				Au	2l/min		
Kamdem 8015889716	2/17/11		O_2		26			100				PR	1l/min		
Trifab gpush 801 425 1585	2/22/11		O_2		60 sccm			125 W				O2 plasma in glass	1 min		
Trifab gpush 801 425 1585	2/23/11		O_2		60 sccm			125 W				O2 plasma	1 min		
Trifab gpush 801 425 1585	2/24/11		O_2		60 sccm			125 W				O2 plasma	1 min		
Trifab gpush 801 425 1585	2/24/11		O_2		60 sccm			125 W				O2 plasma	1 min		
Kamdem 8015889716	2/24/11		O_2		26 sccm			100W				PR	1l/min		
Kamdem 8015889716	2/25/11		SF6		26 sccm			100W				SiN	5min		